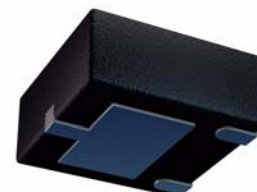


ZXMN2F34MA

20V N-channel enhancement mode MOSFET in DFN322

Summary

$V_{(BR)DSS}$	$R_{DS(on)}$ (Ω)	I_D (A)
20	0.060 @ $V_{GS} = 4.5V$	8.5
	0.120 @ $V_{GS} = 2.5V$	

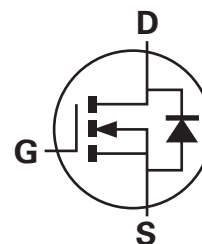


Description

This new generation Trench MOSFET from Zetex features low on-resistance achievable with low (2.5V) gate drive. The 2mm x 2mm DFN package provides superior thermal performance versus alternative leaded devices

Features

- Low on-resistance
- Superior thermal performance (versus to SOT23)
- 2.5V gate drive capability
- DFN 2x2 package

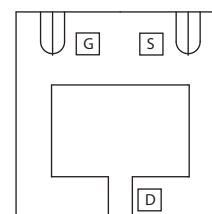


Applications

- Buck/Boost DC-DC Converters
- Motor Control
- LED Lighting

Ordering information

DEVICE	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMN2F34MATA	7	8	3,000



Device marking

1M4

ZXMN2F34MA

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Drain source voltage	V_{DSS}	20	V
Gate source voltage	V_{GS}	± 12	V
Continuous Drain Current @ $V_{GS}=4.5$; $T_A=25^\circ\text{C}^{(b)}$	I_D	5.1	A
@ $V_{GS}=4.5$; $T_A=70^\circ\text{C}^{(b)}$		4.1	A
@ $V_{GS}=4.5$; $T_A=25^\circ\text{C}^{(a)}$		4.0	A
@ $V_{GS}=4.5$; $T_A=25^\circ\text{C}^{(d)}$		8.5	A
Pulsed drain current ^(c)	I_{DM}	19	A
Continuous source current (body diode) ^(b)	I_S	3.1	A
Pulsed source current (body diode) ^(c)	I_{SM}	19	A
Power dissipation at $T_A=25^\circ\text{C}^{(a)}$	P_D	1.35	W
Linear derating factor		10.8	mW/°C
Power dissipation at $T_A=25^\circ\text{C}^{(b)}$	P_D	2.2	W
Linear derating factor		17.8	mW/°C
Power dissipation at $T_A=25^\circ\text{C}^{(d)}$	P_D	6.6	W
Linear derating factor		52.9	mW/°C
Operating and storage temperature range	T_j, T_{stg}	-55 to 150	°C

Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient ^(a)	$R_{\theta JA}$	92.5	°C/W
Junction to ambient ^(b)	$R_{\theta JA}$	56	°C/W
Junction to lead ^(d)	$R_{\theta JL}$	18.9	°C/W

NOTES:

(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

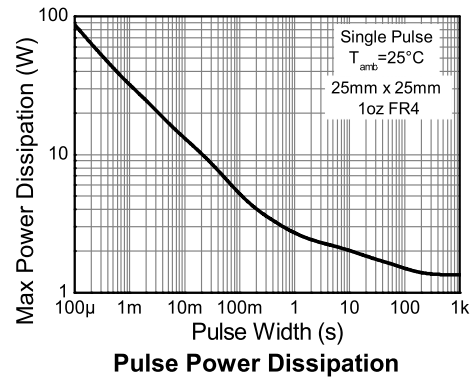
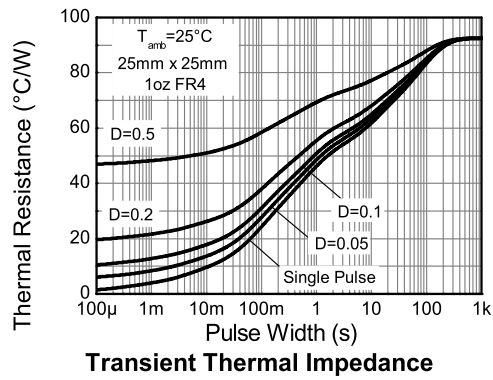
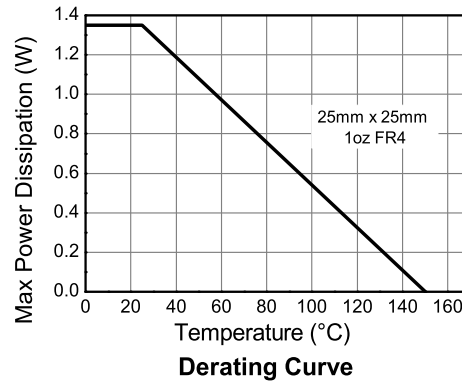
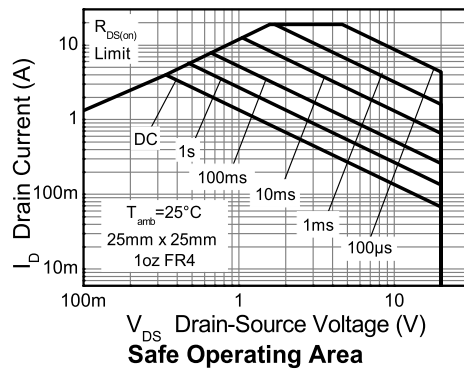
(b) For a device surface mounted on FR4 PCB measured at $t \leq 5$ sec.

(c) Repetitive rating - 25mm x 25mm FR4 PCB, $D=0.02$, pulse width 300 μ s - pulse width limited by maximum junction temperature.

(d) Thermal resistance from junction to solder-point (at end of drain lead).

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Thermal characteristics



ZXMN2F34MA

Electrical characteristics (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Static						
Drain-Source breakdown voltage	V _{(BR)DSS}	20			V	I _D = 250μA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}			1	μA	V _{DS} = 20V, V _{GS} =0V
Gate-Body leakage	I _{GSS}			100	nA	V _{GS} =± 12V, V _{DS} =0V
Gate-Source threshold voltage	V _{GS(th)}	0.5	0.8	1.5	V	I _D = 250μA, V _{DS} =V _{GS}
Static Drain-Source on-state resistance (*)	R _{DS(on)}			0.060 0.120	Ω Ω	V _{GS} = 4.5V, I _D = 2.5A V _{GS} = 2.5V, I _D = 1.0A
Forward transconductance ^(*) (†)	g _{fs}		7.5		S	V _{DS} = 10V, I _D = 2.5A
Dynamic (†)						
Input capacitance	C _{iss}		277		pF	V _{DS} = 10V, V _{GS} =0V f=1MHz
Output capacitance	C _{oss}		65		pF	
Reverse transfer capacitance	C _{rss}		35		pF	
Switching (‡)(†)						
Turn-on-delay time	t _{d(on)}		2.65		ns	V _{DD} = 10V, V _{GS} = 4.5V I _D = 1A R _G ≈ 6.0Ω
Rise time	t _r		4.2		ns	
Turn-off delay time	t _{d(off)}		9.9		ns	
Fall time	t _f		5.1		ns	
Total gate charge	Q _g		2.8		nC	V _{DS} = 10V, V _{GS} = 4.5V I _D = 2.5A
Gate-Source charge	Q _{gs}		0.61		nC	
Gate Drain charge	Q _{gd}		0.63		nC	
Source-drain diode						
Diode forward voltage ^(*)	V _{SD}		0.73	1.2	V	I _S = 1.25A, V _{GS} =0V
Reverse recovery time ^(†)	t _{rr}		6.5		ns	T _J =25°C, I _F =1.65A di/dt=100A/μs
Reverse recovery charge ^(†)	Q _{rr}		1.4		nC	

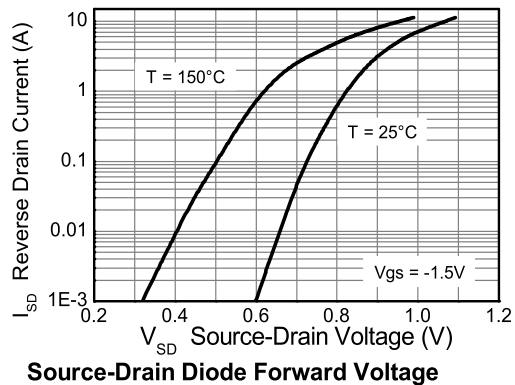
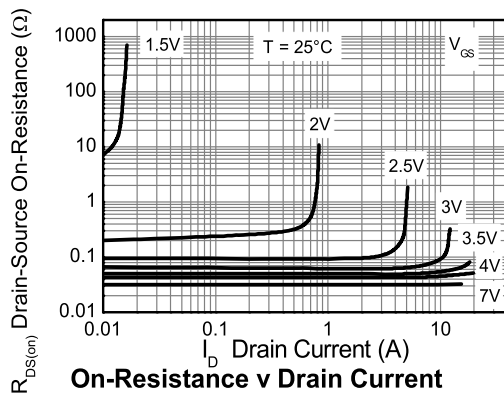
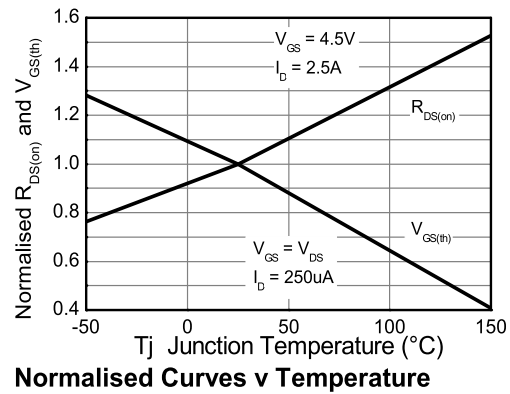
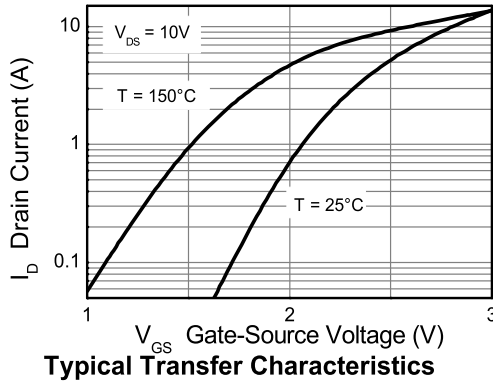
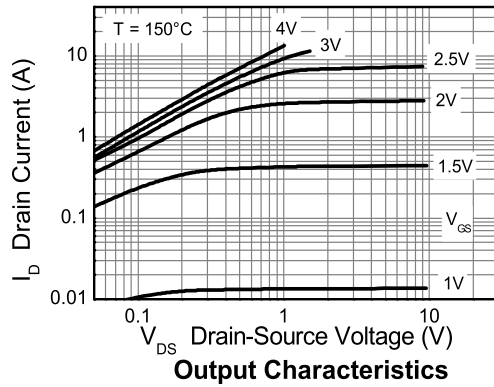
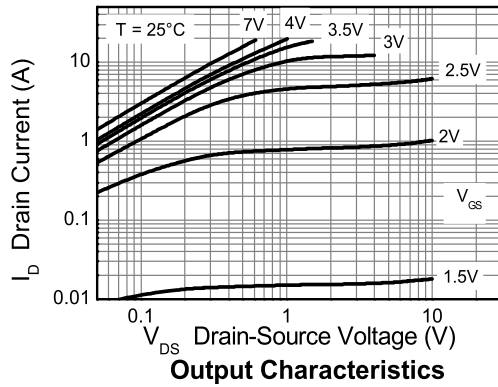
NOTES:

(*) Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.

(†) For design aid only, not subject to production testing.

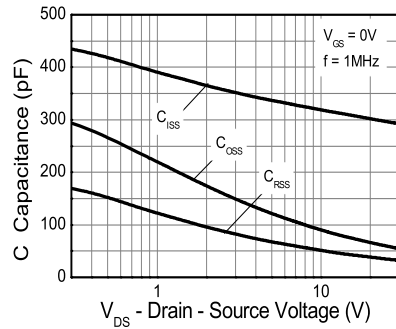
(‡) Switching characteristics are independent of operating junction temperature.

Typical characteristics

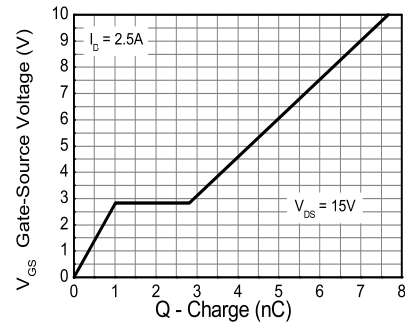


ZXMN2F34MA

Typical characteristics

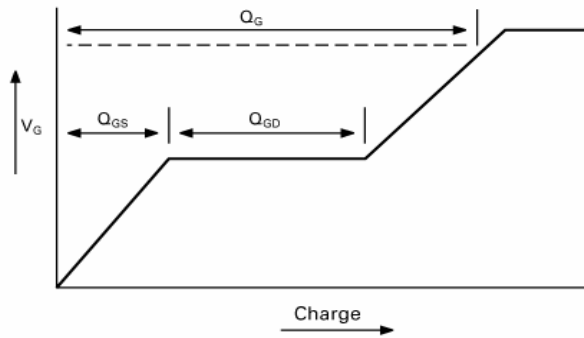


Capacitance v Drain-Source Voltage

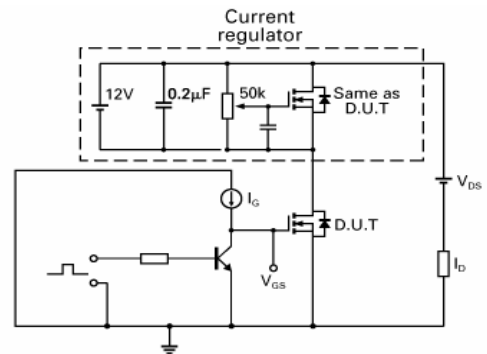


Gate-Source Voltage v Gate Charge

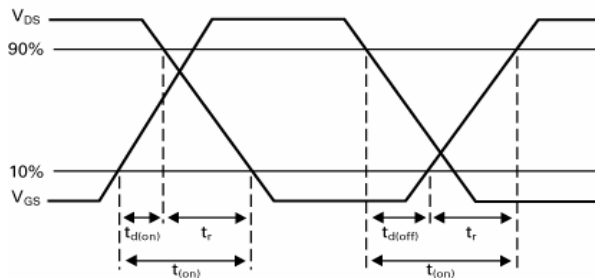
Test circuits



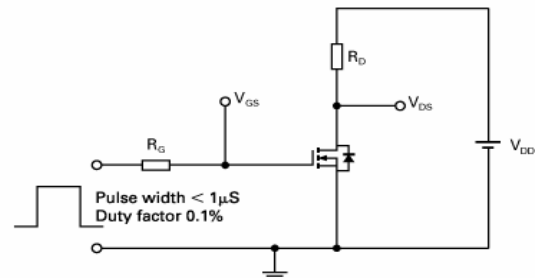
Basic gate charge waveform



Gate charge test circuit



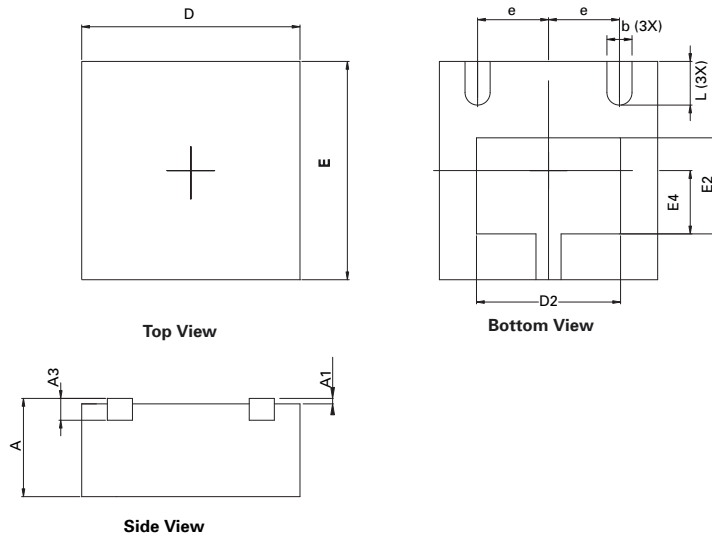
Switching time waveforms



Switching time test circuit

ZXMN2F34MA

Package outline - DFN322



DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.80	1.00	0.0315	0.0393	D2	1.22	1.42	0.0480	0.0559
A1		0.05		0.002	e	0.65 BSC.		0.02559 BSC	
A3	0.153	0.253	0.0060	0.0099	E	1.900	2.100	0.0748	0.0826
b	0.180	0.300	0.0071	0.0118	E2	0.780	0.990	0.0307	0.0389
D	1.900	2.100	0.0748	0.0826	E4	0.480	0.680	0.0189	0.0267
					L	0.300	0.500	0.0118	0.0196

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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